

ABSTRACT OF THE DISCLOSURE

A chemical mechanical polishing method and apparatus are introduced that reduce embedded particles during CMP processing. Throughout the CMP process, the wafer-carrier and the polish platen turn or rotate in the same direction. This enables particles to become embedded in the oxide or other film surface. In the disclosed process, during a final polish step, the wafer carrier or polish platen is turned or rotated in the opposite direction. Embedded particles are then pulled out of the oxide or film, creating a much cleaner wafer. This increases manufacturing yield and decreases manufacturing cost while introducing one additional step and a minor modification to conventional equipment.